

Silicon NPN Power Transistors

2SD1765

DESCRIPTION

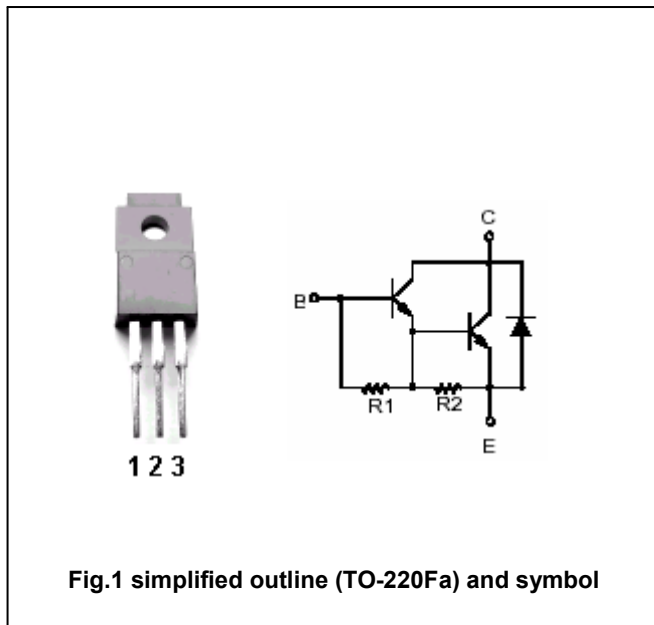
- With TO-220Fa package
- DARLINGTON
- High DC current gain

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector -emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		2	A
I _{CM}	Collector current-peak		3	A
P _C	Collector power dissipation	T _C =25°C	20	W
		T _a =25°C	2	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50μA; I _C =0	100			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA; I _B =0	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A ; I _B =1mA			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3.0	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =2V	1000		10000	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		25		pF

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PACKAGE OUTLINE

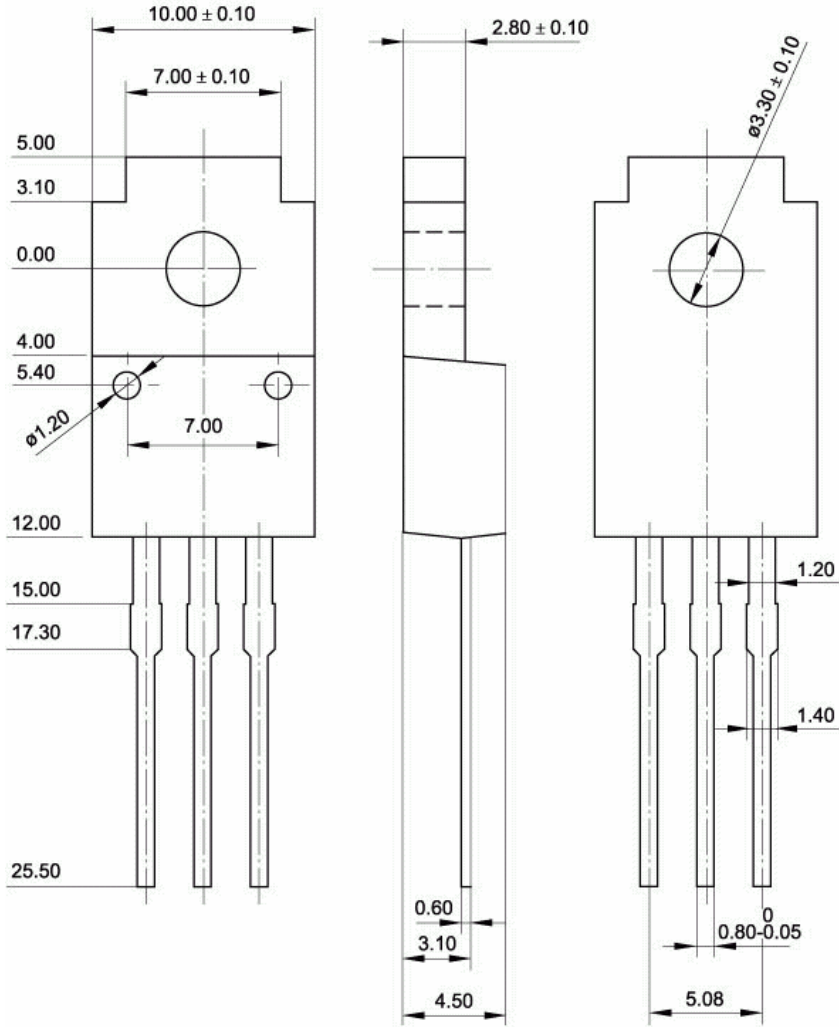


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)